

**Amendments to the Specification**

Please replace the paragraph beginning on page 1, line 5 with the following amended version of that paragraph

**CROSS-REFERENCE TO RELATED APPLICATIONS**

This application is a continuation-in-part claiming priority under 35 USC 120 from US Patent Application No. 10/672,311, filed on September 26, 2003, titled "Method of Porogen Removal from Porous Low-k Films Using UV Radiation," by Adrienne Tipton et al., which application is incorporated herein by reference in its entirety for all purposes, and which in turn claims priority under 35 USC 119(e) from U.S. Provisional Application No. 60/469,433, filed on May 3, 2003, also titled "Method of Porogen Removal from Porous Low-k Films Using UV Radiation." This application is also related to US Patent Application No. 10/404,693, filed on March 31, 2003, titled "Method for Forming Porous Films by Porogen Removal Combined with In Situ Surface Modification," by Raashina Humayun et al.; US Patent Application No. 10/672,305, filed on September 26, 2003, titled "Method for Removal of Porogens from Porous Low-k Films Using Supercritical Fluids," by Adrienne Tipton et al.; and to US Patent Application No. 10/295,965 filed November 15, 2002 by Schulberg, et al., and titled "System for Deposition of Mesoporous Materials," which applications are incorporated herein by reference in its entirety for all purposes.